

Kentaro Kaneko

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/778491/publications.pdf>

Version: 2024-02-01

67
papers

1,840
citations

236925

25
h-index

276875

41
g-index

68
all docs

68
docs citations

68
times ranked

909
citing authors

#	ARTICLE	IF	CITATIONS
1	Epitaxial growth of corundum-structured wide band gap III-oxide semiconductor thin films. Journal of Crystal Growth, 2014, 401, 588-592.	1.5	129
2	Evolution of corundum-structured III-oxide semiconductors: Growth, properties, and devices. Japanese Journal of Applied Physics, 2016, 55, 1202A3.	1.5	106
3	Conductivity control of Sn-doped $\text{In}_{1-x}\text{Ga}_x\text{O}_3$ thin films grown on sapphire substrates. Japanese Journal of Applied Physics, 2016, 55, 1202BA.	1.5	91
4	Fabrication of Highly Crystalline Corundum-Structured $\text{In}_{1-x}\text{Ga}_x\text{O}_3/\text{Fe}_x\text{O}_3$ Alloy Thin Films on Sapphire Substrates. Applied Physics Express, 0, 2, 075501.	2.4	83
5	Growth and Band Gap Control of Corundum-Structured $\text{In}_{1-x}\text{Al}_x\text{O}_3$ Thin Films on Sapphire by Spray-Assisted Mist Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2012, 51, 100207.	1.5	83
6	Homoepitaxial growth of beta gallium oxide films by mist chemical vapor deposition. Japanese Journal of Applied Physics, 2016, 55, 1202B8.	1.5	79
7	Reduction in edge dislocation density in corundum-structured $\text{In}_{1-x}\text{Ga}_x\text{O}_3$ layers on sapphire substrates with quasi-graded $\text{In}_{1-x}\text{Al}_x\text{O}_3$ buffer layers. Applied Physics Express, 2016, 9, 071101.	2.4	76
8	A power device material of corundum-structured $\text{In}_{1-x}\text{Ga}_x\text{O}_3$ fabricated by MIST EPITAXY [®] technique. Japanese Journal of Applied Physics, 2018, 57, 02CB18.	1.5	76
9	Electrical properties of $\text{In}_2\text{O}_3/\text{In}_{1-x}\text{Ga}_x\text{O}_3$ pn heterojunction diode and band alignment of the heterostructure. Applied Physics Letters, 2018, 113, .	3.3	74
10	Growth characteristics of corundum-structured $\text{In}_{1-x}\text{Al}_x\text{O}_3/\text{Ga}_2\text{O}_3$ heterostructures on sapphire substrates. Journal of Crystal Growth, 2016, 436, 150-154.	1.5	72
11	Evaluation of Misfit Relaxation in $\text{In}_{1-x}\text{Ga}_x\text{O}_3$ Epitaxial Growth on $\text{In}_{1-x}\text{Al}_x\text{O}_3$ Substrate. Japanese Journal of Applied Physics, 2012, 51, 020201.	1.5	63
12	Band gap and function engineering for novel functional alloy semiconductors: Bloomed as magnetic properties at room temperature with $\text{In}_{1-x}\text{Ga}_x\text{O}_3$. Journal of Applied Physics, 2013, 113, .	2.5	62
13	Growth of corundum-structured In_2O_3 thin films on sapphire substrates with Fe_2O_3 buffer layers. Journal of Crystal Growth, 2013, 364, 30-33.	1.5	62
14	Enhanced thermal stability of alpha gallium oxide films supported by aluminum doping. Japanese Journal of Applied Physics, 2015, 54, 030301.	1.5	50
15	Growth of corundum-structured $\text{In}_{1-x}\text{Al}_x\text{O}_3$ alloy thin films on sapphire substrates with buffer layers. Journal of Crystal Growth, 2014, 401, 670-672.	1.5	46
16	Evaluation of band alignment of $\text{In}_{1-x}\text{Ga}_x\text{O}_3/\text{In}_{1-x}\text{Al}_x\text{O}_3$ by X-ray photoelectron spectroscopy. Japanese Journal of Applied Physics, 2018, 57, 040314.	1.5	46
17	Electrical characterization of Si-doped n-type $\text{In}_{1-x}\text{Ga}_x\text{O}_3$ on sapphire substrates. MRS Advances, 2018, 3, 171-177.	0.9	41
18	Control of Crystal Structure of Ga_2O_3 on Sapphire Substrate by Introduction of $\text{In}_{1-x}\text{Al}_x\text{O}_3$ Buffer Layer. Physica Status Solidi (B): Basic Research, 2018, 255, 1700326.	1.5	41

#	ARTICLE	IF	CITATIONS
19	Ultra-wide bandgap corundum-structured p-type $\text{(Ir,Ga)Ga}_2\text{O}_3$ alloys for Ga_2O_3 electronics. Applied Physics Letters, 2021, 118, .	3.3	36
20	Corundum-structured Ga_2O_3 Cr_2O_3 Fe_2O_3 alloy system for novel functions. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 2467-2470.	0.8	35
21	Crack-free thick ($\sim 1/4 \mu\text{m}$) Ga_2O_3 films on sapphire substrates with $\text{(Al,Ga)}_2\text{O}_3$ buffer layers. Japanese Journal of Applied Physics, 2016, 55, 1202B4.	1.5	32
22	Prospects for phase engineering of semi-stable Ga_2O_3 semiconductor thin films using mist chemical vapor deposition. Journal of Applied Physics, 2022, 131, .	2.5	31
23	Growth and Band Gap Control of Corundum-Structured $\text{(AlGa)}_2\text{O}_3$ Thin Films on Sapphire by Spray-Assisted Mist Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2012, 51, 100207.	1.5	29
24	Ultrasonic-assisted mist chemical vapor deposition of In_2O_3 and related oxide compounds. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 1225-1228.	0.8	28
25	Enhancement of epitaxial lateral overgrowth in the mist chemical vapor deposition of Ga_2O_3 by using a-plane sapphire substrate. Japanese Journal of Applied Physics, 2019, 58, 120912.	1.5	28
26	Growth of rocksalt-structured $\text{Mg}_x\text{Zn}_{1-x}\text{O}$ ($x \geq 0.5$) films on MgO substrates and their deep-ultraviolet luminescence. Applied Physics Express, 2016, 9, 111102.	2.4	26
27	Thermal stability of Ga_2O_3 films grown on c-plane sapphire substrates via mist-CVD. AIP Advances, 2020, 10, .	1.3	26
28	Surface termination structure of Ga_2O_3 film grown by mist chemical vapor deposition. Applied Physics Letters, 2016, 108, 251602.	3.3	25
29	Oriented growth of beta gallium oxide thin films on yttrium-stabilized zirconia substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1596-1599.	0.8	23
30	Tin oxide coating by nonvacuum-based mist chemical vapor deposition on stainless steel separators for polymer electrolyte fuel cells. Japanese Journal of Applied Physics, 2018, 57, 117103.	1.5	22
31	Evaluation of Misfit Relaxation in Ga_2O_3 Epitaxial Growth on Al_2O_3 Substrate. Japanese Journal of Applied Physics, 2012, 51, 020201.	1.5	20
32	Growth and metal-oxide-semiconductor field-effect transistors of corundum-structured alpha indium oxide semiconductors. Applied Physics Express, 2015, 8, 095503.	2.4	19
33	Pure deep-ultraviolet cathodoluminescence from rocksalt-structured MgZnO grown with carbon-free precursors. Applied Physics Express, 2019, 12, 052011.	2.4	18
34	Establishment of a growth route of crystallized rutile GeO_2 thin film ($\sim 1/4 \mu\text{m/h}$) and its structural properties. Applied Physics Letters, 2021, 119, .	3.3	18
35	Deep-Ultraviolet Luminescence of Rocksalt-Structured $\text{Mg}_x\text{Zn}_{1-x}\text{O}$ ($x \geq 0.5$) Films on MgO Substrates. Journal of Electronic Materials, 2018, 47, 4356-4360.	2.2	15
36	Faraday effect of bismuth iron garnet thin film prepared by mist CVD method. Japanese Journal of Applied Physics, 2015, 54, 063001.	1.5	14

#	ARTICLE	IF	CITATIONS
37	Thermal stability of $\text{In}_{1-x}\text{Ga}_x\text{O}_3$ films grown on c-plane sapphire substrates with an Al composition up to 90%. Japanese Journal of Applied Physics, 2021, 60, SBBD13.	1.5	13
38	Initial nucleation scheme of Ga_2O_3 on (0001) sapphire by mist CVD for the growth of In -phase. Japanese Journal of Applied Physics, 2021, 60, 055501.	1.5	13
39	Unpredicted surface termination of $\text{In-Fe}_2\text{O}_3$ (0001) film grown by mist chemical vapor deposition. Surface Science, 2017, 660, 9-15.	1.9	9
40	Preparation of yttrium iron garnet thin films by mist chemical vapor deposition method and their magneto-optical properties. Japanese Journal of Applied Physics, 2014, 53, 05FB17.	1.5	8
41	Identification of free and bound exciton emission of MgO single crystal in vacuum ultraviolet spectral range. Applied Physics Letters, 2021, 119, .	3.3	7
42	Novel p-type oxides with corundum structure for gallium oxide electronics. Journal of Materials Research, 2022, 37, 651-659.	2.6	7
43	Vertical Schottky barrier diodes of In_2O_3 fabricated by mist epitaxy. , 2015, , .		6
44	Corundum-Structured In_2O_3 as a Wide-Bandgap Semiconductor for Electrical Devices. MRS Advances, 2017, 2, 301-307.	0.9	6
45	Impact of hydrochloric acid on the epitaxial growth of In_2O_3 films on (0001) $\text{In-Al}_2\text{O}_3$ substrates by mist CVD. Applied Physics Express, 2020, 13, 075504.	2.4	6
46	Analysis of Deep Traps in Mist Chemical Vapor Deposition-Grown n-Type $\text{In-Ga}_2\text{O}_3$ by Photocapacitance Method. Physica Status Solidi (B): Basic Research, 2021, 258, 2000622.	1.5	6
47	Fabrication of $\text{Cu}_2\text{ZnSnS}_4$ Thin Films by Ultrasonic-Atomized Mist Methods. Zairyo/Journal of the Society of Materials Science, Japan, 2015, 64, 410-413.	0.2	4
48	Fabrication by Mist CVD Method and Evaluation of Corundum Structured Oxide Semiconductor Thin Films. Zairyo/Journal of the Society of Materials Science, Japan, 2010, 59, 686-689.	0.2	4
49	Mist Deposition Technique as a Green Chemical Route for Synthesizing Oxide and Organic Thin Films. Materials Research Society Symposia Proceedings, 2009, 1220, 4061.	0.1	3
50	Crystal Structure of Non-Doped and Sn-Doped $\text{In}(\text{GaFe})_2\text{O}_3$ Thin Films.. Materials Research Society Symposia Proceedings, 2013, 1494, 147-152.	0.1	3
51	Recent Advancement of Semiconductor Materials and Devices. Zairyo/Journal of the Society of Materials Science, Japan, 2017, 66, 58-65.	0.2	3
52	Fabrication of Lithium-Based Oxide Thin Films by Ultrasonic-Assisted Mist CVD Technique. Zairyo/Journal of the Society of Materials Science, Japan, 2011, 60, 994-997.	0.2	3
53	Metal Separator of Fuel Cells Coated with Highly Conductive and Highly Corrosion-Resistant Oxide Thin Films. Zairyo/Journal of the Society of Materials Science, Japan, 2017, 66, 639-643.	0.2	3
54	Mist Chemical Vapor Deposition Growth of In_2O_3 Films Using Indium Oxide Powder as Source Precursor. Physica Status Solidi (B): Basic Research, 0, , 2100414.	1.5	3

#	ARTICLE	IF	CITATIONS
55	Study on corundum-structured p-type iridium oxide thin films and band alignment at iridium oxide/gallium oxide hetero-junction. , 2018, , .		2
56	Fabrication of Corundum-Structured $\hat{\text{I}}_{\pm}(\text{InFe})_2\text{O}_3$ Alloy Films on Sapphire Substrates by Inserting $\hat{\text{I}}_{\pm}\text{Fe}_2\text{O}_3$ Buffer Layer. Materials Research Society Symposia Proceedings, 2013, 1494, 221-225.	0.1	1
57	Characterization of band offset in $\hat{\text{I}}_{\pm}(\text{Al}_{x}\text{Ga}_{1-x})_2\text{O}_3/\hat{\text{I}}_{\pm}\text{Ga}_2\text{O}_3$ heterostructures. , 2016, , .		1
58	Corundum-structured $\hat{\text{I}}_{\pm}\text{Ga}_2\text{O}_3$ -based alloys for future power device applications. , 2017, , .		1
59	Synthesis of Metastable or Non-Equilibrium-Phased Oxides by the Mist CVD method. Zairyo/Journal of the Society of Materials Science, Japan, 2021, 70, 369-373.	0.2	1
60	VUV emission properties of rocksalt-structured MgZnO microcrystals prepared on quartz glass substrates. Physica Status Solidi (B): Basic Research, 0, , 2100354.	1.5	1
61	Crystal Growth and Device Applications of Corundum-Structured Gallium Oxide. Zairyo/Journal of the Society of Materials Science, Japan, 2016, 65, 631-637.	0.2	0
62	Fabrication of $\hat{\text{I}}_{\pm}\text{Ga}_2\text{O}_3$ thin films using properties. , 2016, , .		0
63	Research of Semiconductor Materials That Emit in the Vacuum Ultraviolet Region of 200 nm or Less. Zairyo/Journal of the Society of Materials Science, Japan, 2021, 70, 727-731.	0.2	0
64	Ga₂O₃ Crystal for Power Device. Journal of the Institute of Electrical Engineers of Japan, 2017, 137, 693-696.	0.0	0
65	An Nightmare of the Day before Christmas Eve. Zairyo/Journal of the Society of Materials Science, Japan, 2019, 68, 731-732.	0.2	0
66	Synthesis of Metastable or Non-Equilibrium Phased Oxides and Their Physical Properties. Zairyo/Journal of the Society of Materials Science, Japan, 2019, 68, 733-738.	0.2	0
67	Synthesis of High-Quality $\hat{\text{I}}_{\pm}\text{Ga}_2\text{O}_3$ thin films on Sapphire Substrates with Introduction of Buffer Layers. Zairyo/Journal of the Society of Materials Science, Japan, 2020, 69, 707-711.	0.2	0